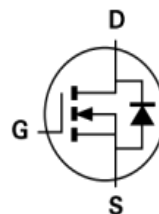


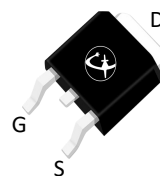
MAIN CHARACTERISTICS

I_D	100A
V_{DSS}	20V
$R_{DS(on)}$ -typ (@ $V_{GS}=10V$ $T_c=25^{\circ}C$)	2.6m Ω



FEATURES

- 20V Trench DMOS technology
- Low on-state resistance
- Fast switching
- Improved dv/dt capability



TO-252

APPLICATIONS

- Power management
- Portable devices
- Load switch

Product specification classification

Part Number	Package	Mode Name	Pack
LT100N02AD	TO-252	LT100N02AD	Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Continue Drain Current	I_D	100	A
Pulsed Drain Current (Note1)	I_{DM}	360	A
Power Dissipation	P_D	90	W
Single Pulse Avalanche Energy	E_{AS}	120	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.8	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	40	°C/W

Note1:Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	BV_{DSS}	20	-	-	V
Drain-Source Leakage Current	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 12\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	0.4	-	1	V
Drain-Source On-State Resistance	$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}$	$R_{DS(on)}$	-	2.6	3.6	m Ω
	$V_{GS} = 2.5\text{ V}, I_D = 20\text{ A}$		-	3.1	6	m Ω
Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 10\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	3200	-	pF
Output Capacitance		C_{oss}	-	458	-	pF
Reverse Transfer Capacitance		C_{rss}	-	445	-	pF
Turn-on Delay Time(Note2)	$V_{GS}=4.5\text{ V}, V_{DD}=10\text{ V}, R_G=1.8\text{ }\Omega, I_D=30\text{ A}$	$t_{d(ON)}$	-	9.6	-	ns
Rise Time(Note2)		t_r	-	38	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	63	-	ns
Fall Time(Note2)		t_f	-	52	-	ns
Total Gate Charge(Note2)	$I_D = 30\text{ A}, V_{DD} = 10\text{ V}, V_{GS} = 4.5\text{ V}$	Q_G	-	47	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	3.5	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	19	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	100	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	360	A
Drain-Source Diode Forward Voltage	$I_{SD} = 30\text{ A}$	V_{SD}	-	-	1.2	V
Reverse Recovery Time(Note2)	$I_{SD} = 30\text{ A}, V_{GS} = 0\text{ V}, dI_F / dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	22	-	ns
Reverse Recovery Charge(Note2)		Q_{rr}	-	11	-	nC

Note2:Pulse test: 300 μ s pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

Figure 1: Output Characteristics

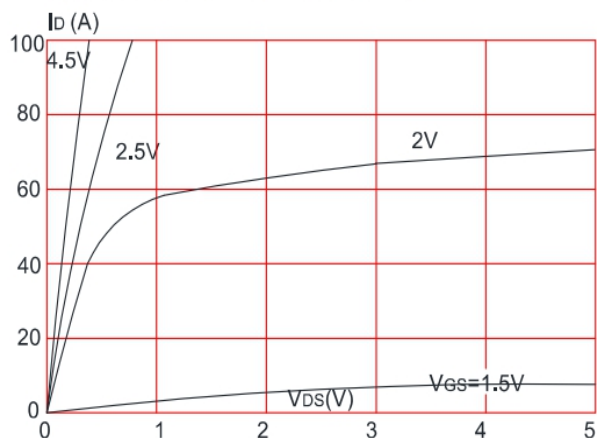


Figure 2: Typical Transfer Characteristics

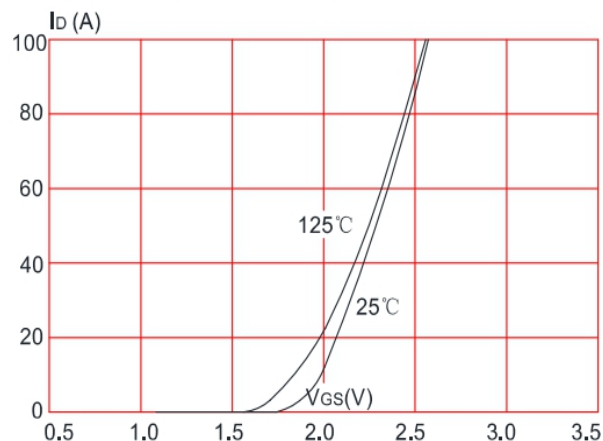


Figure 3: On-resistance vs. Drain Current

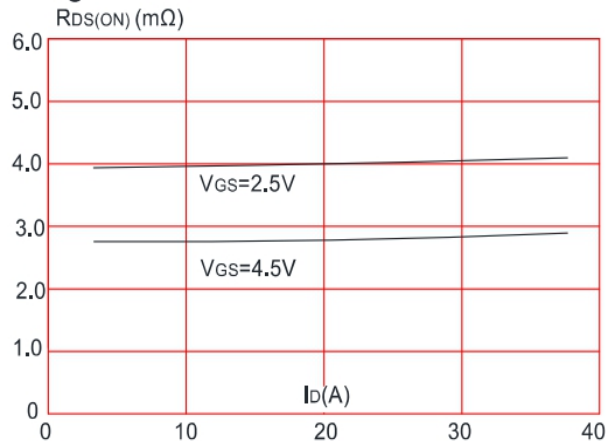


Figure 4: Body Diode Characteristics

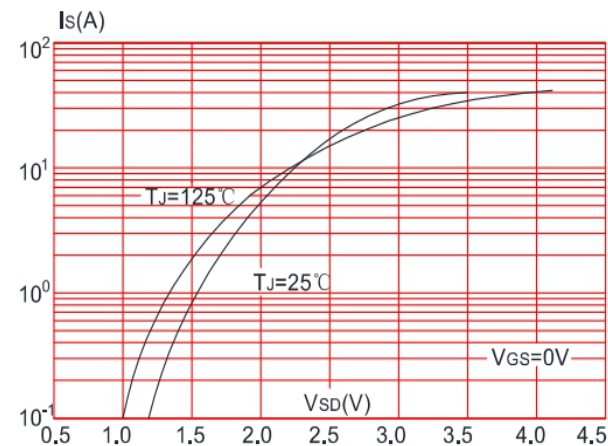


Figure 5: Gate Charge Characteristics

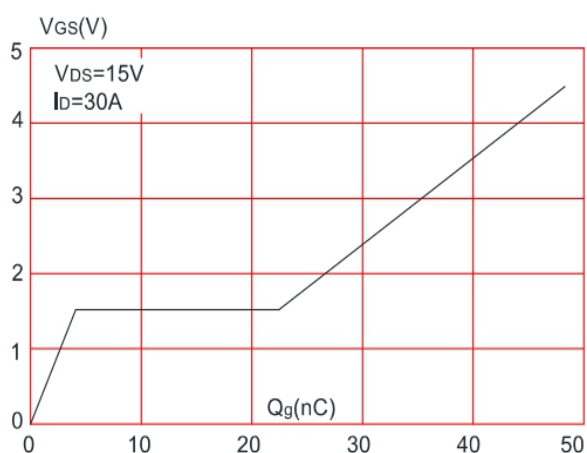
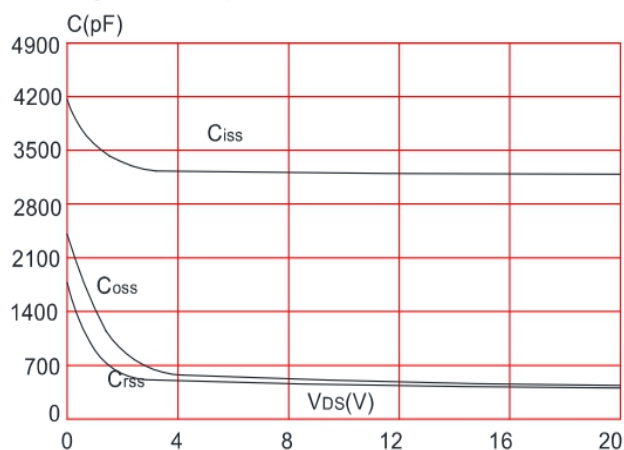


Figure 6: Capacitance Characteristics



RATINGS AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

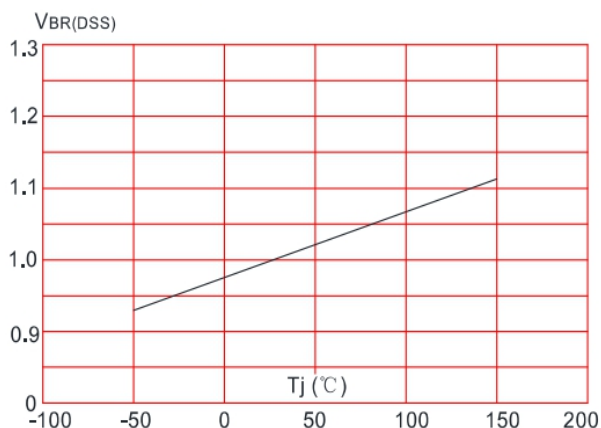


Figure 8: Normalized on Resistance vs. Junction Temperature

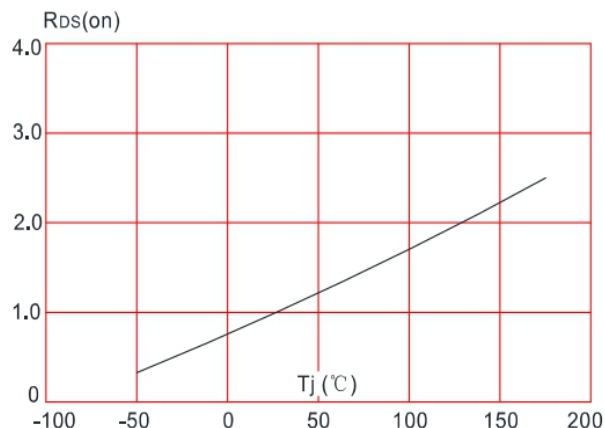


Figure 9: Maximum Safe Operating Area

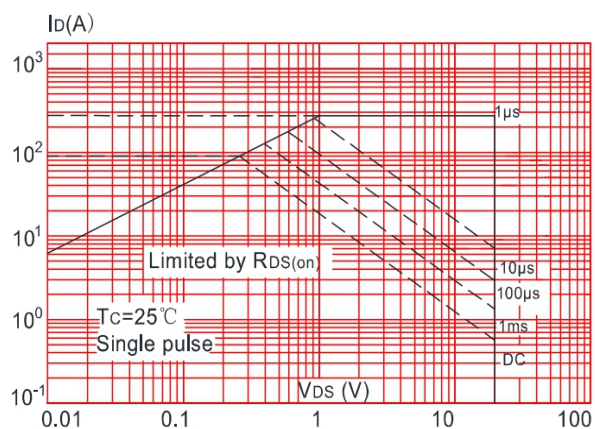


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

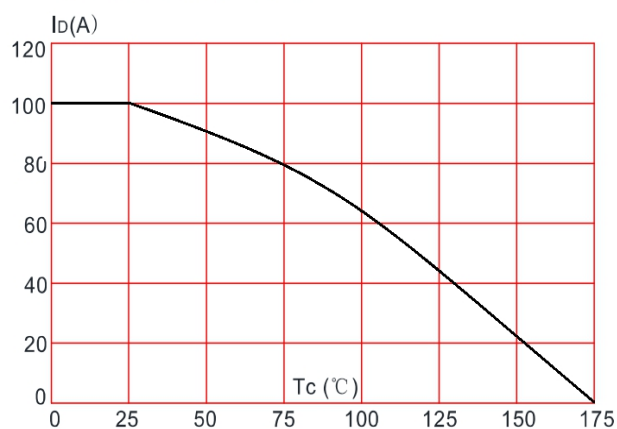
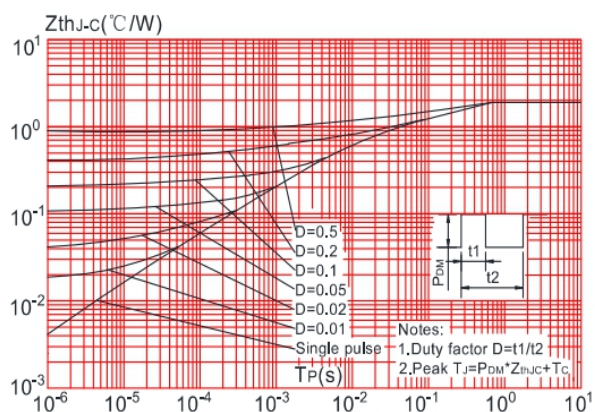
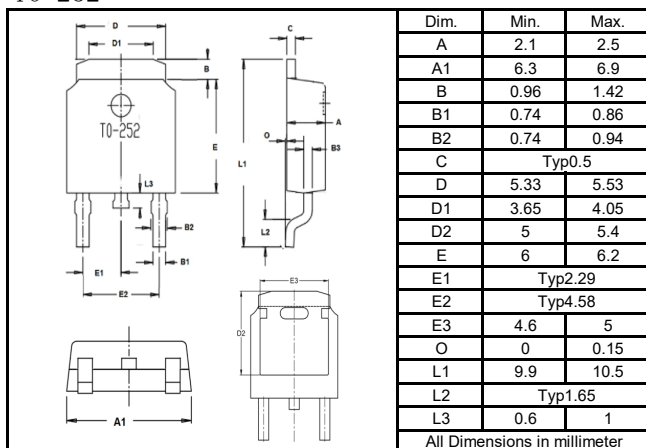


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

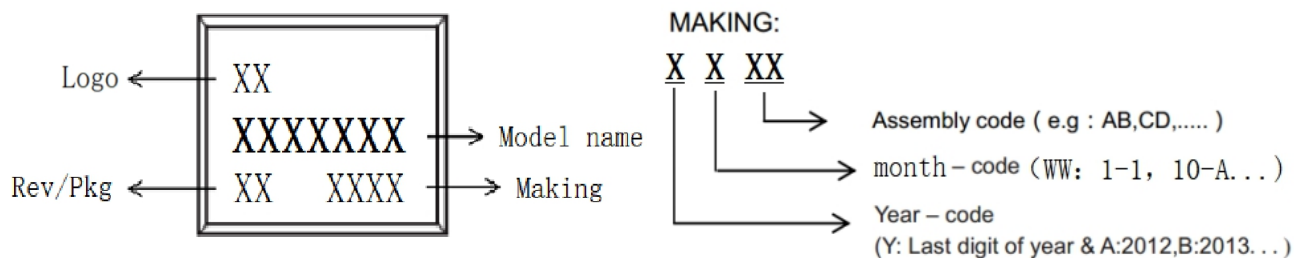


Package Outline Dimensions millimeters

TO-252



Marking on the body



packing instruction

PKG	Minimal Package	Mini Box	Box
TO-252			
	2500pcs/disk	5000pcs/disk	25000pcs/box



LT100N02AD

N-Channel Trench Power MOSFET

Notice

All product, product specifications and data are subject to change without notice to improve. The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying power exceeding normal rated

power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

<http://www.lxmicro.com>

Revision History

Rev	Changes	Date
1.0	First version	2025/6/30